

Fig.1

Inventor: Donghang YAN et al.
Title: Heterojunction Organic Semiconductor Field
Effect Transistor (FET) with a Gate Insulation
Layer and Manufacturing Process Thereof
Attorney Docket No.: 33419-190319

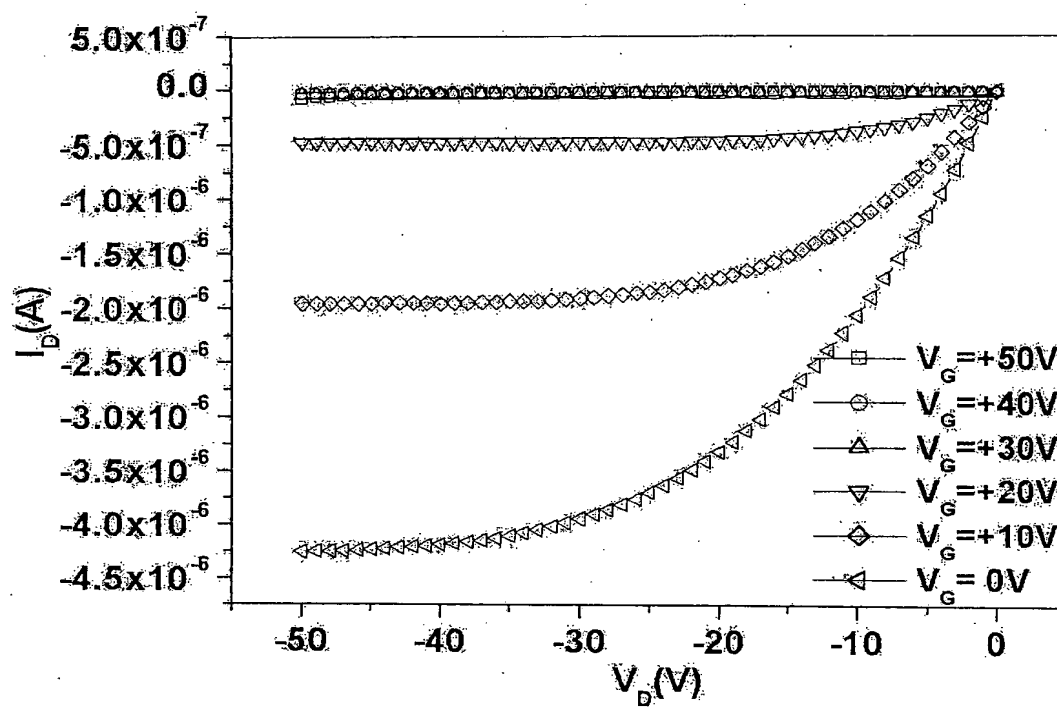


Fig.2

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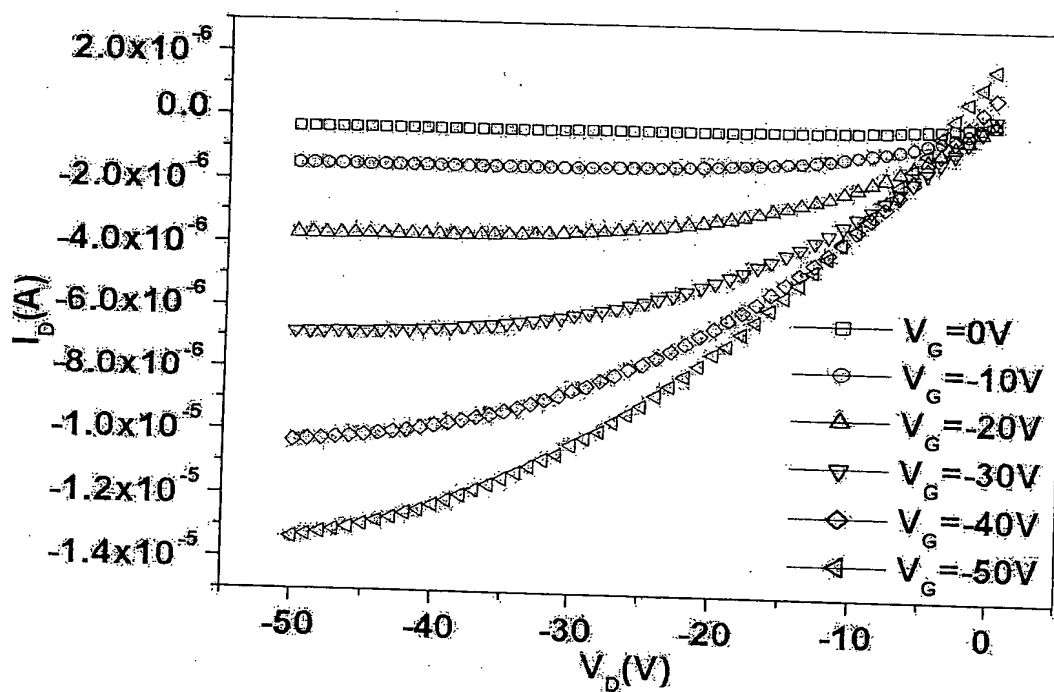


Fig.3

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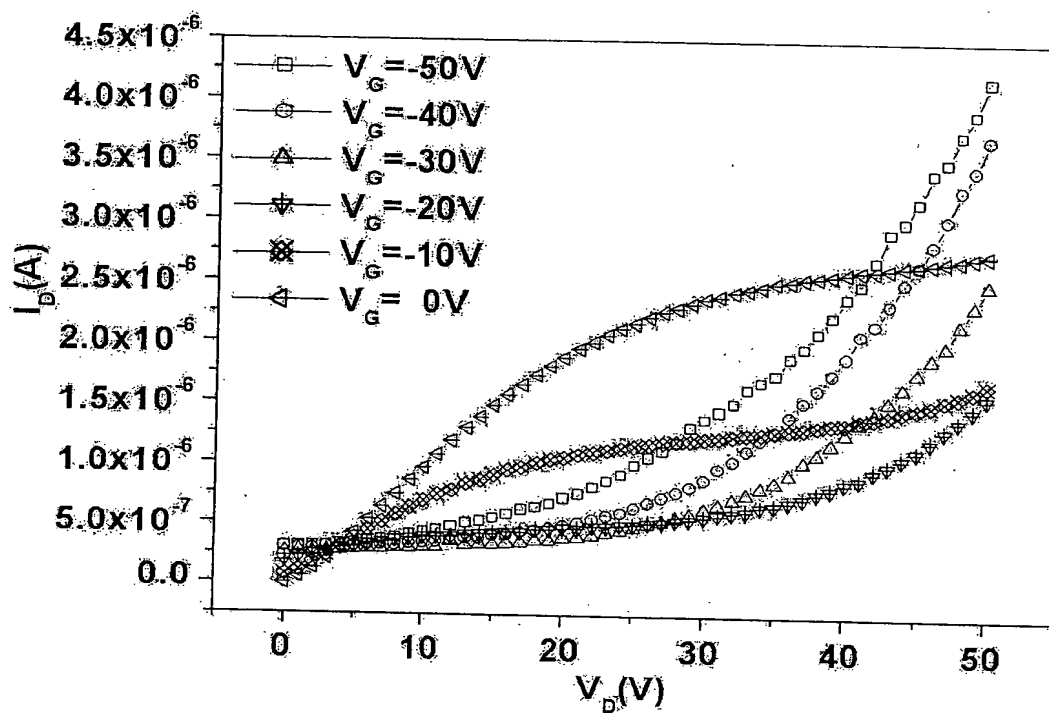


Fig.4

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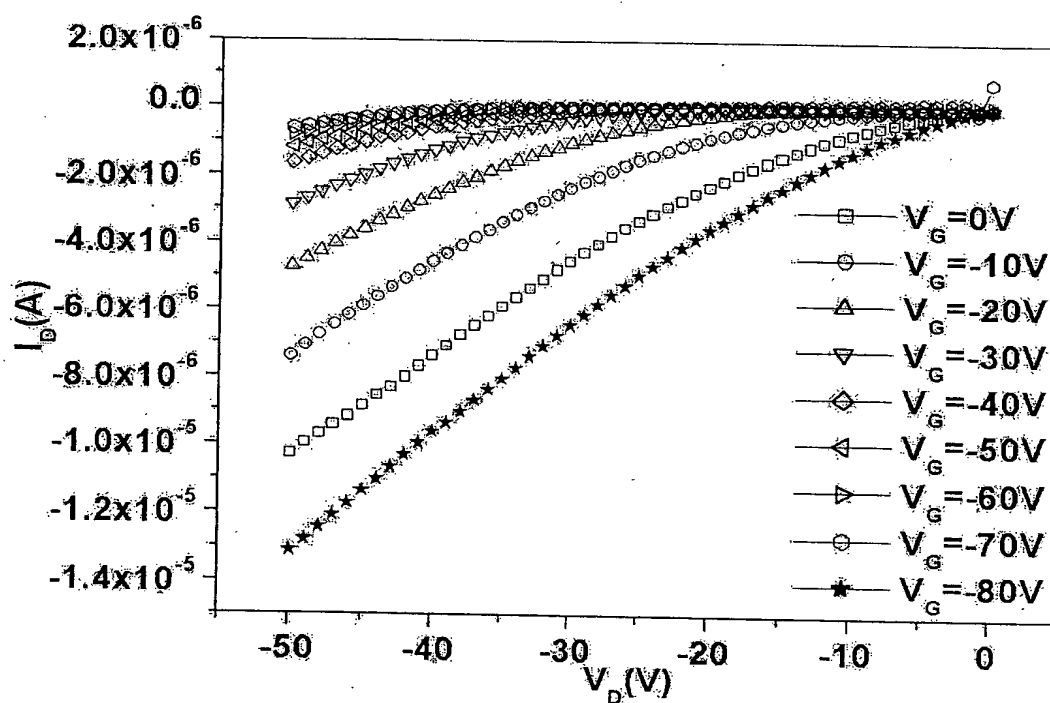


Fig.5

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